

Silicon NPN Power Transistors

2SC1520

**DESCRIPTION**

- With TO-202 package
- High voltage
- High transition frequency

**APPLICATIONS**

- For color TV chroma output and video output applications

**PINNING(see Fig.2)**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

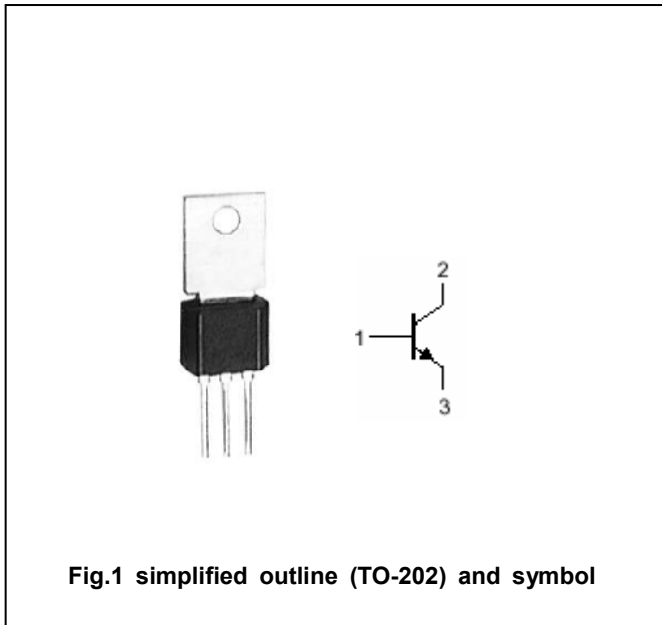


Fig.1 simplified outline (TO-202) and symbol

**Absolute maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	250	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	250	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		0.2	A
P <sub>C</sub>	Collector power dissipation	T <sub>a</sub> =25°C	1.0	W
		T <sub>C</sub> =25°C	10	
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =50mA ; I <sub>B</sub> =5mA			2.0	V
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =1mA; I <sub>B</sub> =0	250			V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =150V ; I <sub>E</sub> =0			0.1	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			0.1	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =10mA ; V <sub>CE</sub> =10V	40		200	
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =50V; f=1MHz			4.5	pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =10mA ; V <sub>CB</sub> =30V		80		MHz

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PACKAGE OUTLINE

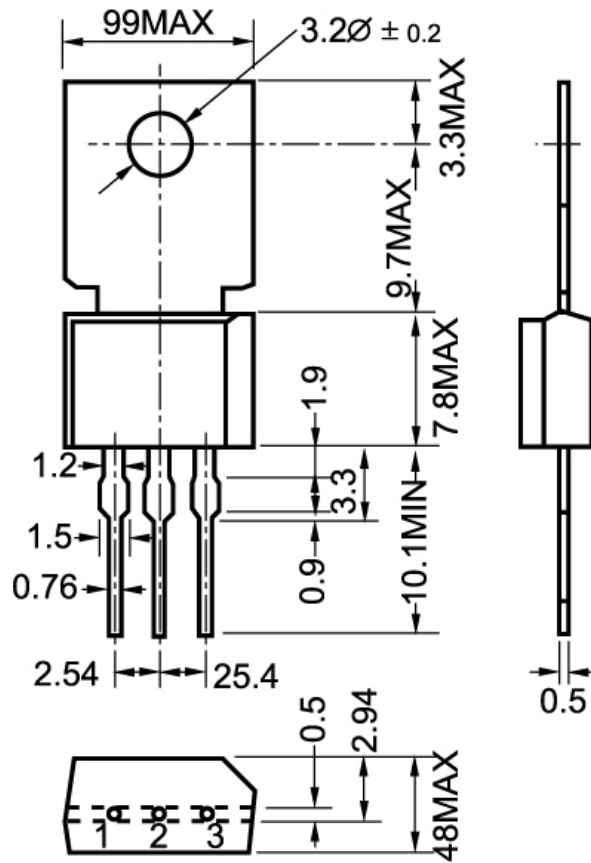


Fig.2 outline dimensions